# **Complementary Silicon High-Power Transistors**

... PowerBase complementary transistors designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc—to—dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055 and MJ2955.

• Current-Gain - Bandwidth-Product @ IC = 1.0 Adc

 $f_T = 0.8 \text{ MHz (Min)} - \text{NPN}$ 

= 2.2 MHz (Min) - PNP

Safe Operating Area — Rated to 60 V and 120 V, Respectively

#### \*MAXIMUM RATINGS

Rating	Symbol	2N3055A MJ2955A	MJ15015 MJ15016	Unit
Collector–Emitter Voltage	VCEO	60	120	Vdc
Collector–Base Voltage	V <sub>CBO</sub>	100	200	Vdc
Collector–Emitter Voltage Base Reversed Biased	VCEV	100	200	Vdc
Emitter-Base Voltage	VEBO	7.0		Vdc
Collector Current — Continuous	Ic	1	5	Adc
Base Current	IB	7.0		Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	115 0.65	180 1.03	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.52	0.98	°C/W

<sup>\*</sup> Indicates JEDEC Registered Data. (2N3055A)

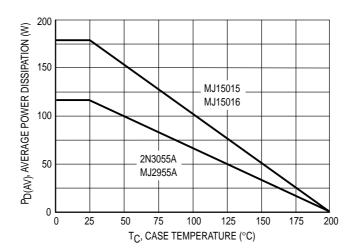


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

#### REV<sub>1</sub>

## 2N3055A MJ15015\* MJ2955A PNP MJ15016\*

\*Motorola Preferred Device

15 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60, 120 VOLTS
115, 180 WATTS



CASE 1-07 TO-204AA (TO-3)



### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS (1)				_	
*Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 200 mAdc, I <sub>B</sub> = 0)	2N3055A, MJ2955A MJ15015, MJ15016	VCEO(sus)	60 120	_ _	Vdc
Collector Cutoff Current (VCE = 30 Vdc, VBE(off) = 0 Vdc) (VCE = 60 Vdc, VBE(off) = 0 Vdc)	2N3055A, MJ2955A MJ15015, MJ15016	<sup>I</sup> CEO	_ _	0.7 0.1	mAdc
*Collector Cutoff Current (V <sub>CEV</sub> = Rated Value, V <sub>BE(off)</sub> = 1.5 Vdc)	2N3055A, MJ2955A MJ15015, MJ15016	ICEV	_	5.0 1.0	mAdc
Collector Cutoff Current (V <sub>CEV</sub> = Rated Value, V <sub>BE(off)</sub> = 1.5 Vdc, T <sub>C</sub> = 150°C)	2N3055A, MJ2955A MJ15015, MJ15016	ICEV	_ _	30 6.0	mAdc
Emitter Cutoff Current (VEB = 7.0 Vdc, I <sub>C</sub> = 0)	2N3055A, MJ2955A MJ15015, MJ15016	I <sub>EBO</sub>	_	5.0 0.2	mAdc
SECOND BREAKDOWN					•
Second Breakdown Collector Current with Base (t = 0.5 s non–repetitive) (V <sub>CE</sub> = 60 Vdc)	Forward Biased 2N3055A, MJ2955A MJ15015, MJ15016	I <sub>S/b</sub>	1.95 3.0		Adc
ON CHARACTERISTICS (1)		4.14.14			
DC Current Gain (I <sub>C</sub> = 4.0 Adc, V <sub>CE</sub> = 2.0 Vdc) (I <sub>C</sub> = 4.0 Adc, V <sub>CE</sub> = 4.0 Vdc) (I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 4.0 Vdc)	1 3 3 B	hFE	10 20 5.0	70 70 —	_
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 4.0 Adc, I <sub>B</sub> = 400 mAdc) (I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 3.3 Adc) (I <sub>C</sub> = 15 Adc, I <sub>B</sub> = 7.0 Adc)	ON.	VCE(sat)	_ _ _	1.1 3.0 5.0	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 4.0 Adc, V <sub>CE</sub> = 4.0 Vdc)		V <sub>BE(on)</sub>	0.7	1.8	Vdc
DYNAMIC CHARACTERISTICS		•		•	
Current–Gain — Bandwidth Product (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 4.0 Vdc, f = 1.0 MHz)	2N3055A, MJ15015 MJ2955A, MJ15016	fΤ	0.8 2.2	6.0 18	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>ob</sub>	60	600	pF
SWITCHING CHARACTERISTICS (2N3055A or	nly)				
RESISTIVE LOAD					
Delay Time		<sup>t</sup> d		0.5	μs
Rise Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 4.0 \text{ Adc},$	t <sub>r</sub>	_	4.0	μs
Storage Time	$I_{B1} = I_{B2} = 0.4 \text{ Adc},$ $t_p = 25  \mu\text{s} \text{ Duty Cycle} \leq 2\%$	t <sub>S</sub>	_	3.0	μs
Fall Time		t <sub>f</sub>	_	6.0	μs

<sup>(1)</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2%. \* Indicates JEDEC Registered Data. (2N3055A)

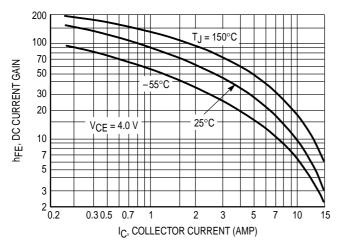


Figure 2. DC Current Gain

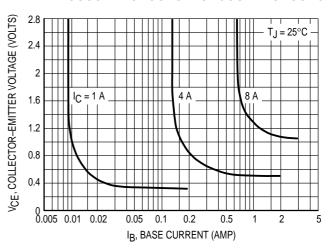


Figure 3. Collector Saturation Region

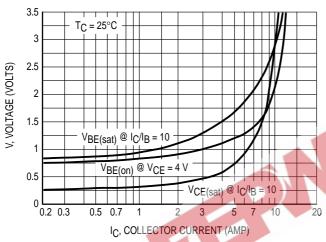


Figure 4. "On" Voltages

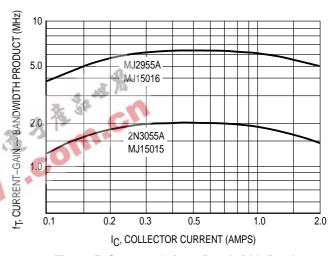


Figure 5. Current-Gain — Bandwidth Product

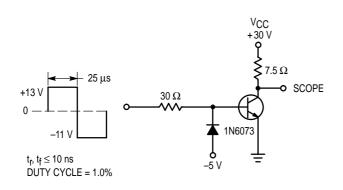


Figure 6. Switching Times Test Circuit (Circuit shown is for NPN)

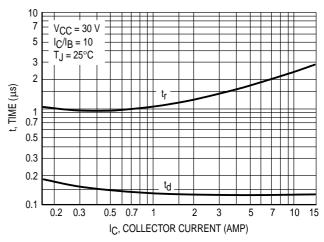
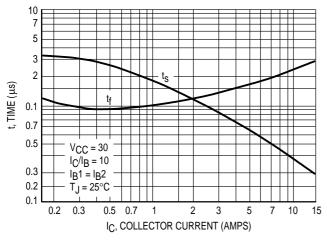


Figure 7. Turn-On Time



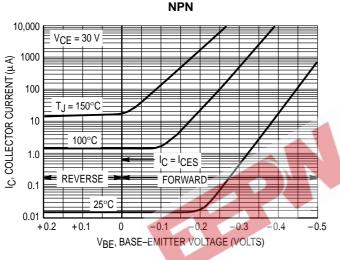
400 2N3055A MJ15015 200 C, CAPACITANCE (pF) MJ2955A MJ15016 50 30 20 2.0 20 50 200 500 1000 1.0 10 100 VR, REVERSE VOLTAGE (VOLTS)

Figure 8. Turn-Off Times

Figure 9. Capacitances

**PNP** 

#### **COLLECTOR CUT-OFF REGION**



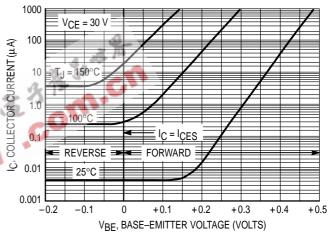
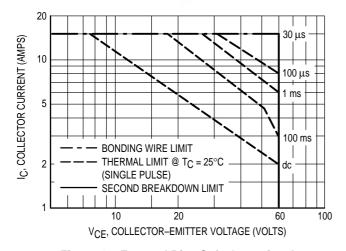


Figure 10. 2N3055A, MJ15015

Figure 11. MJ2955A, MJ15016



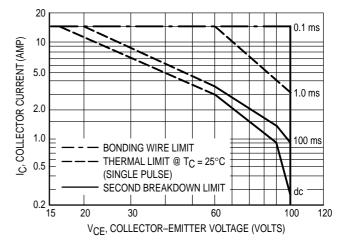


Figure 12. Forward Bias Safe Operating Area 2N3055A, MJ2955A

tion than the curves indicate.

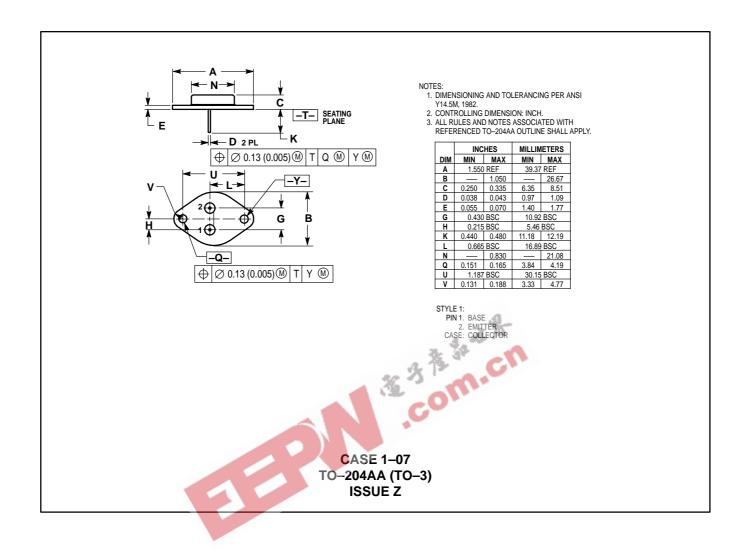
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe Operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipa-

The data of Figures 12 and 13 is based on  $T_C = 25^{\circ}C$ ;  $T_{J(pk)}$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

Figure 13. Forward Bias Safe Operating Area

MJ15015, MJ15016

#### PACKAGE DIMENSIONS





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